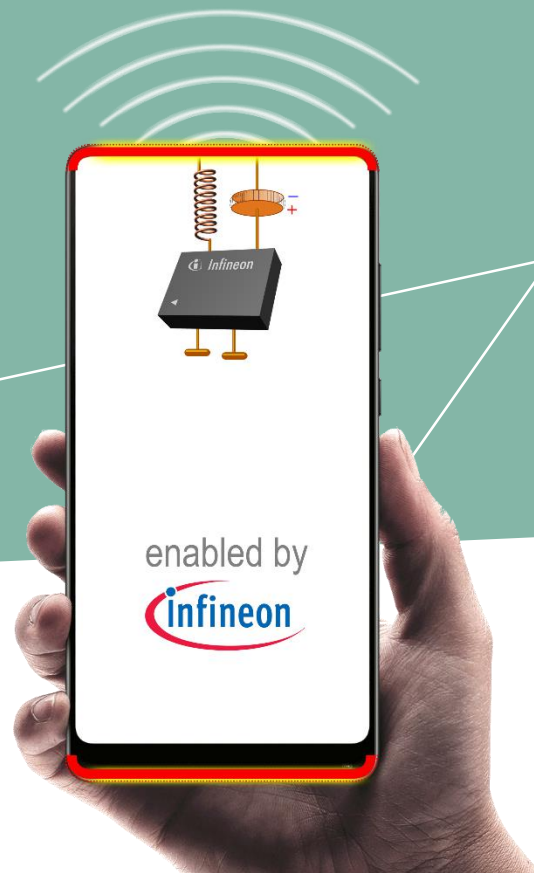


Antenna Tuning Switches for Cellular Handheld Devices

Valentyn Solomko
Infineon Technologies AG
2022-XII-9



Applications for Antenna Tuners



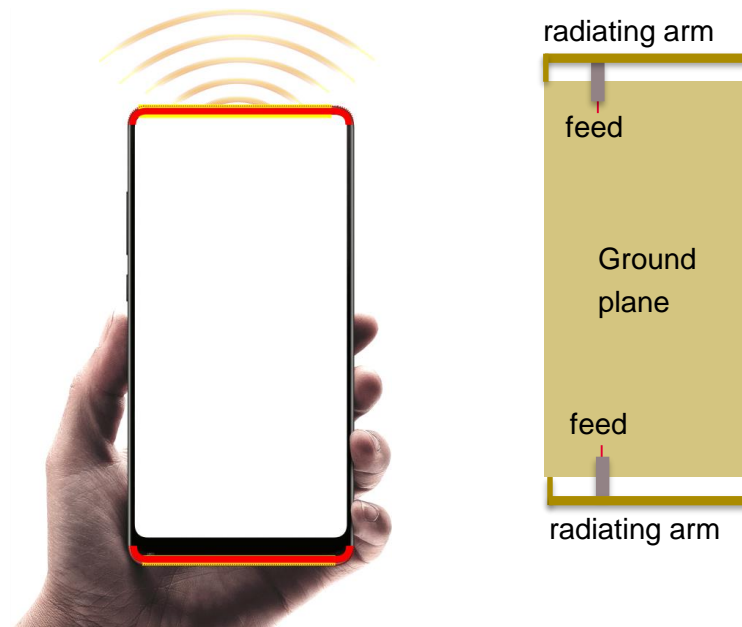
Antenna Evolution in Cellular Phones

Monopole Antenna



1990-th

Inverted-F Antenna

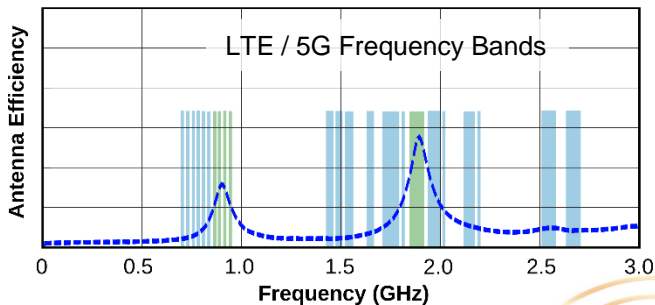


2000-nd

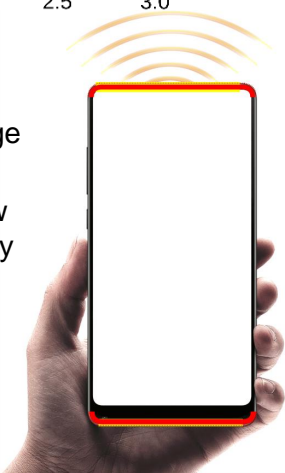
2010-th

Need for Antenna Tuning

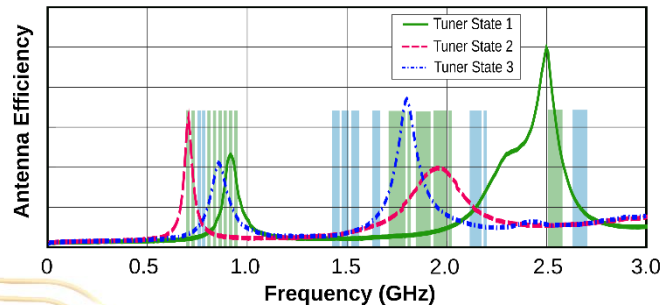
Fixed Mobile Phone Antenna



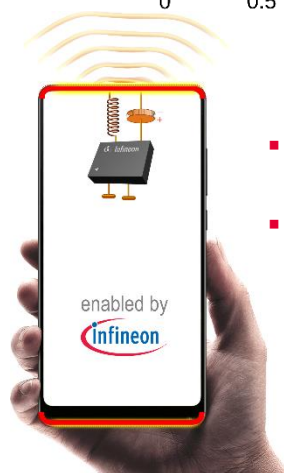
- LTE / 5G require wide frequency range coverage at sub-6 GHz
- Intrinsic integrated antennas have low power efficiency and limited frequency coverage
- User interaction with the phone may substantially change (degrade) the antenna performance



Tunable Mobile Phone Antenna



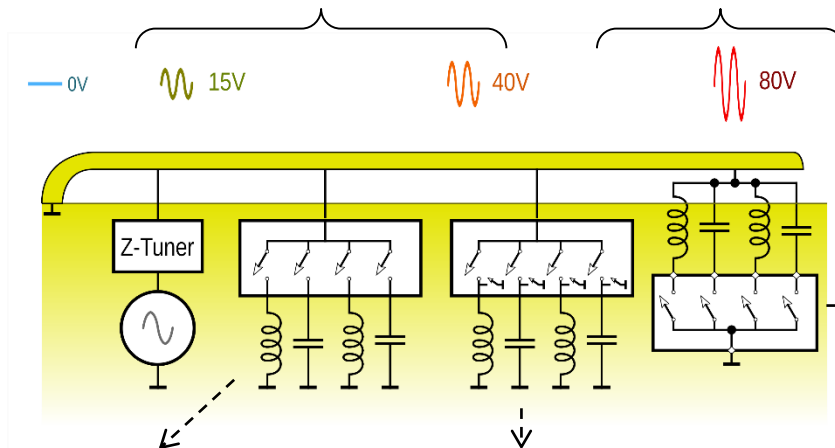
- Antenna tuning (AT) technique improves power efficiency and frequency coverage
- AT resolves the trade-off between phone appearance and electrical performance
- AT became de-facto standard in modern smartphones



Antenna Tuning Topologies

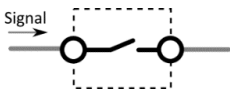
Middle RF voltage handling class tuners
up to **45 V_{RF.MAX}**

High RF voltage handling class tuners
up to **100 V_{RF.MAX}**



Series Switch : reflective open

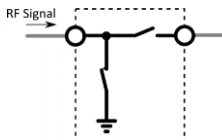
RF Signal



“Breaks” or
“makes” the RF
signal path

Series Switch : reflective short

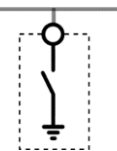
RF Signal



“Breaks” the RF signal
path and shorts open
end to ground

Shunt Switch

RF Signal



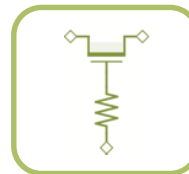
Shunts RF line
to ground



OFF-state
switch

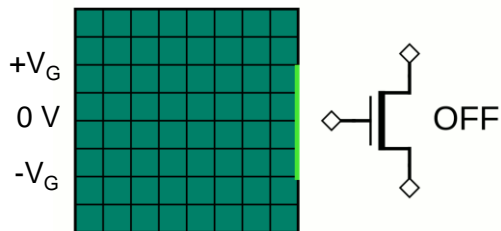
series
resonance
possible!

AT Switch Design at a Glance

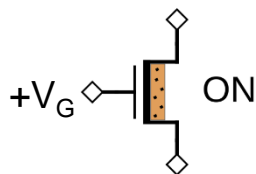
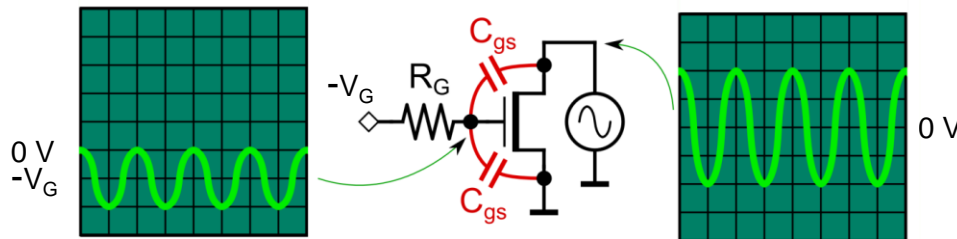


MOS Switch Transistor

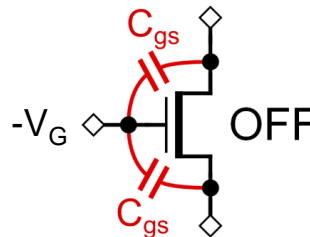
RF Switch Transistor



Linear RF Switch



ON-Resistance
 $R_{ON} = R_{channel}$



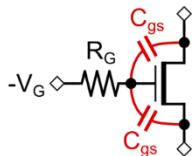
OFF-Capacitance

$$C_{OFF} = \frac{1}{2} C_{gs}$$

- $R_{ON}C_{OFF}$ is a Figure of Merit (FOM) for a given RF-switch technology
- FOM = 70 fs ... 110 fs for state-of-art dedicated CMOS technologies

R_{ON} / C_{OFF} Scaling

$$C_{OFF1} = \frac{1}{2} C_{gs}$$



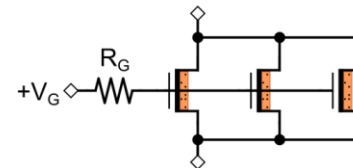
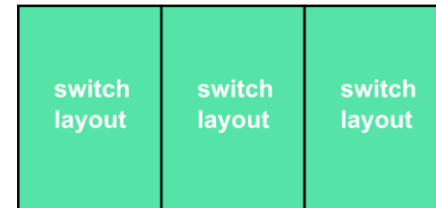
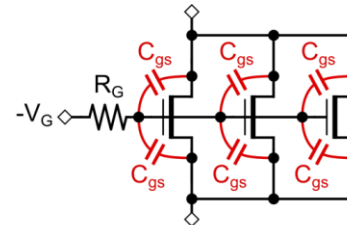
$$R_{ON1} = R_{channel}$$

- R_{ON}/C_{OFF} are linearly-scaled with transistor width
- R_{ON} and C_{OFF} are inversely-proportional to each other
- Switches with lower R_{ON} are **larger in size**
- Ratio $R_{ON} \cdot C_{OFF}$ for switches remain constant no matter how transistors are sized:

$$R_{ON1} C_{OFF1} = R_{ON2} C_{OFF2} = FOM$$

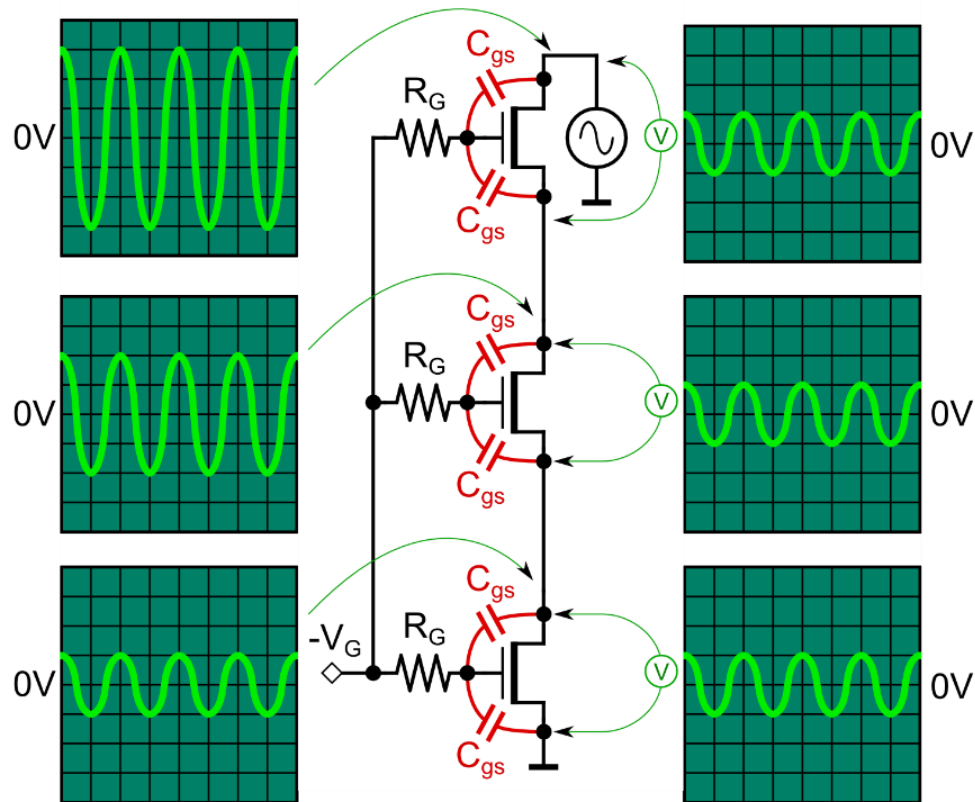
However, $R_{ON} \cdot C_{OFF}$ ratio of actual product is **higher** due to routing/package/PCB parasitics!

$$C_{OFF2} = 3 \cdot \frac{1}{2} C_{gs}$$



$$R_{ON2} = \frac{1}{3} R_{channel}$$

High RF Voltage Handling



- In state-of-art dedicated switch technologies
 - $R_{ON}C_{OFF} = 70 \text{ fs} \dots 110 \text{ fs}$
 - Single transistor can handle 3 V...4 V RF voltage

- Number of stacked devices is linearly-proportional to maximum RF voltage
- Total R_{ON} and C_{OFF} is partitioned according to the number of stacked devices:

$$R_{ON\Sigma} = R_{ON} \cdot \text{STK}$$

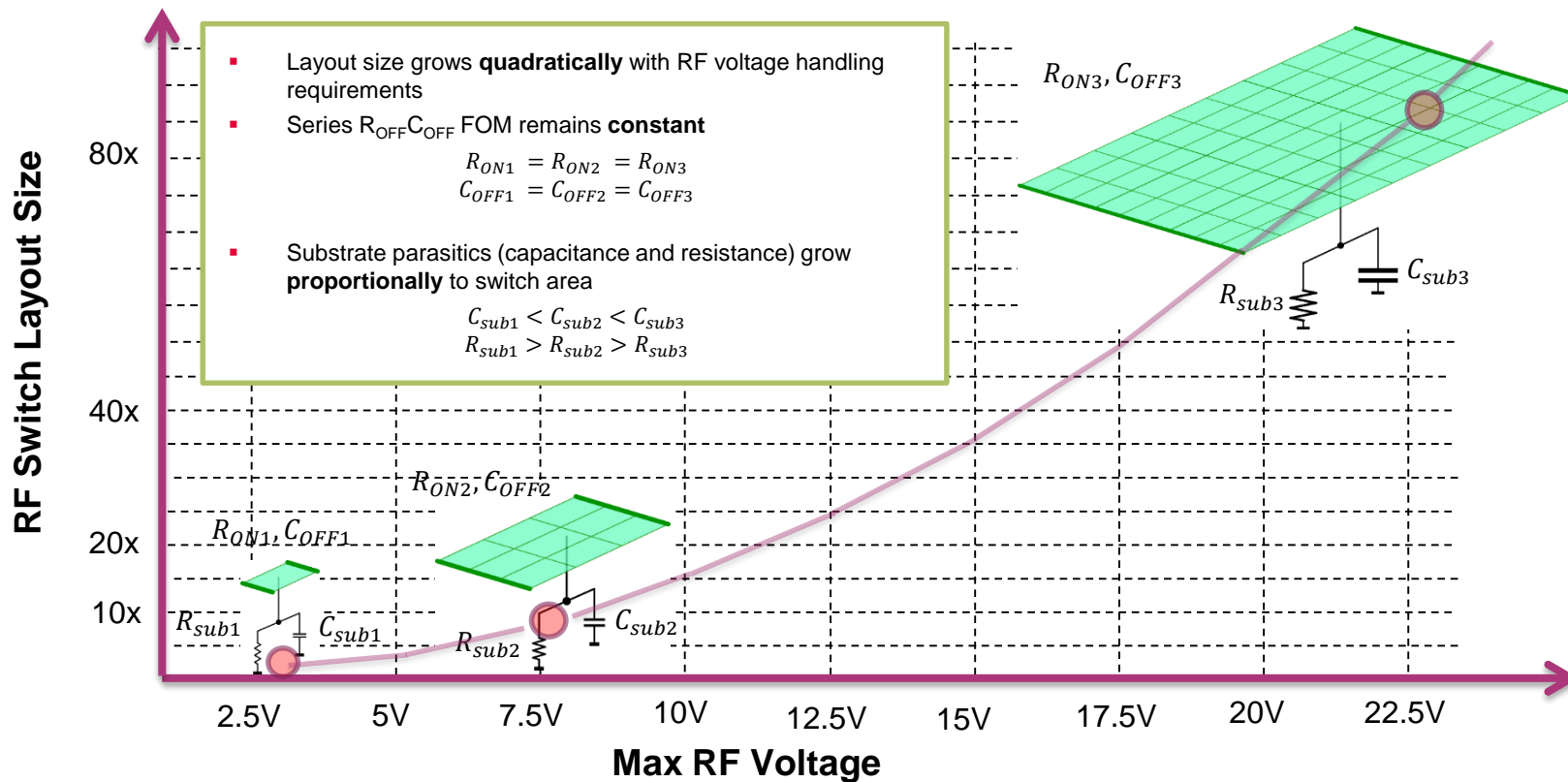
$$C_{OFF\Sigma} = C_{OFF} / \text{STK}$$

- $R_{ON} \cdot C_{OFF}$ product remain constant no matter how transistors are sized and stacked:

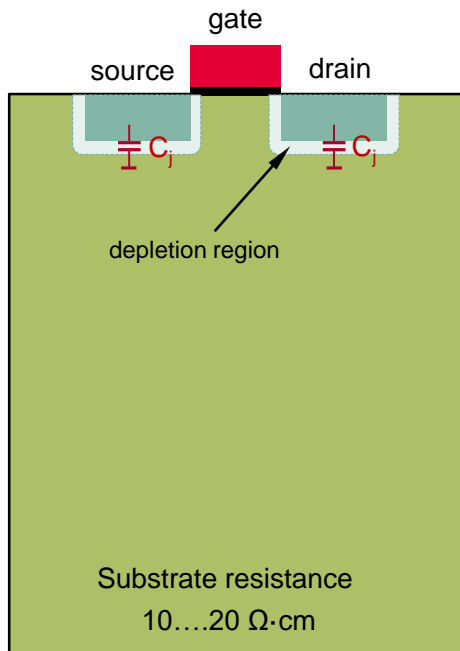
$$R_{ON\Sigma} \cdot C_{OFF\Sigma} = R_{ON} \cdot C_{OFF}$$

- High-voltage switches are **large in size**

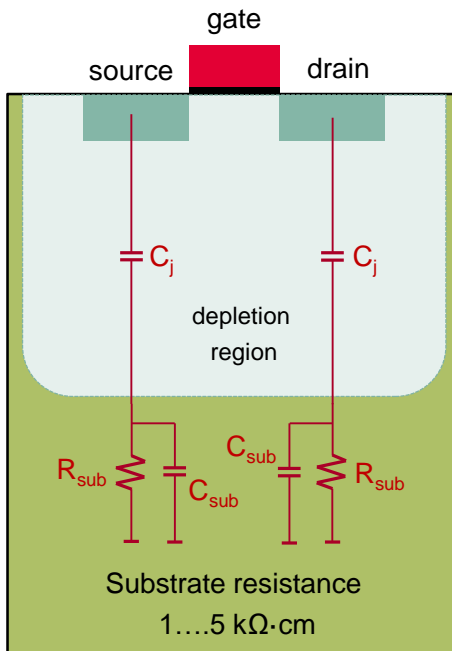
High RF Voltage Handling – Layout Scaling and Parasitics



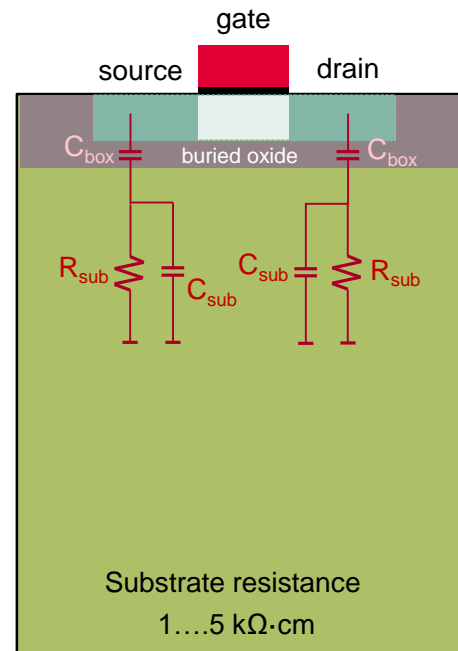
Dedicated versus Standard MOS Transistor



Standard bulk-CMOS



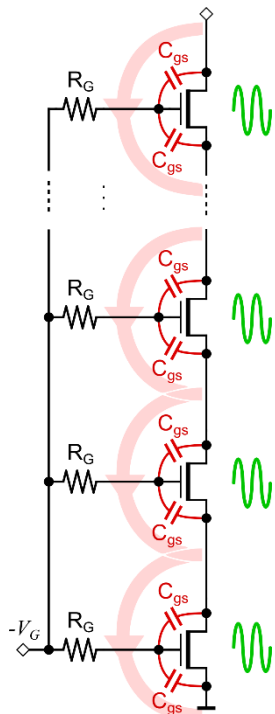
Dedicated RF switch
bulk-CMOS



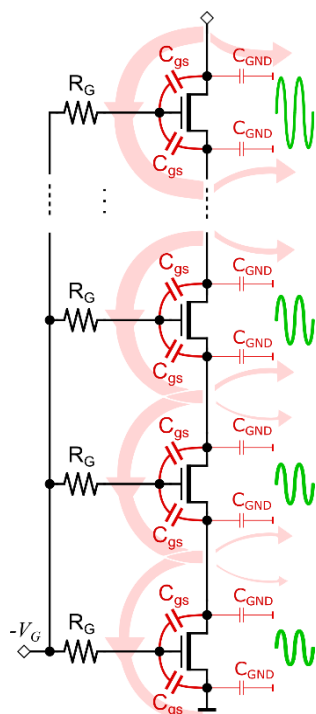
Dedicated RF switch
SOI-CMOS

Effect of Substrate Parasitics and Compensation Thereof

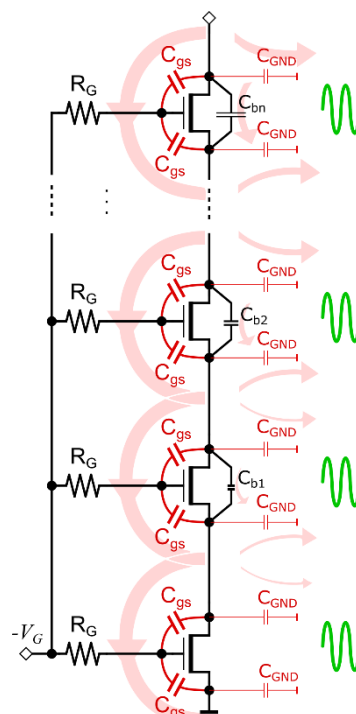
Perfect Voltage Division



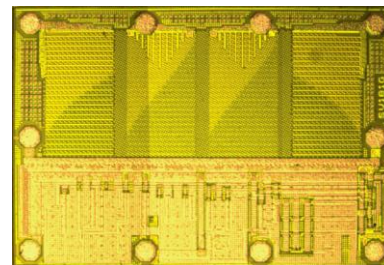
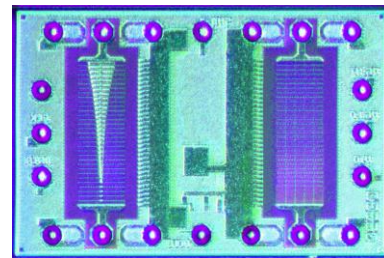
Distorted Voltage Division



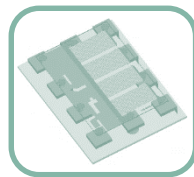
Equalized Voltage Division



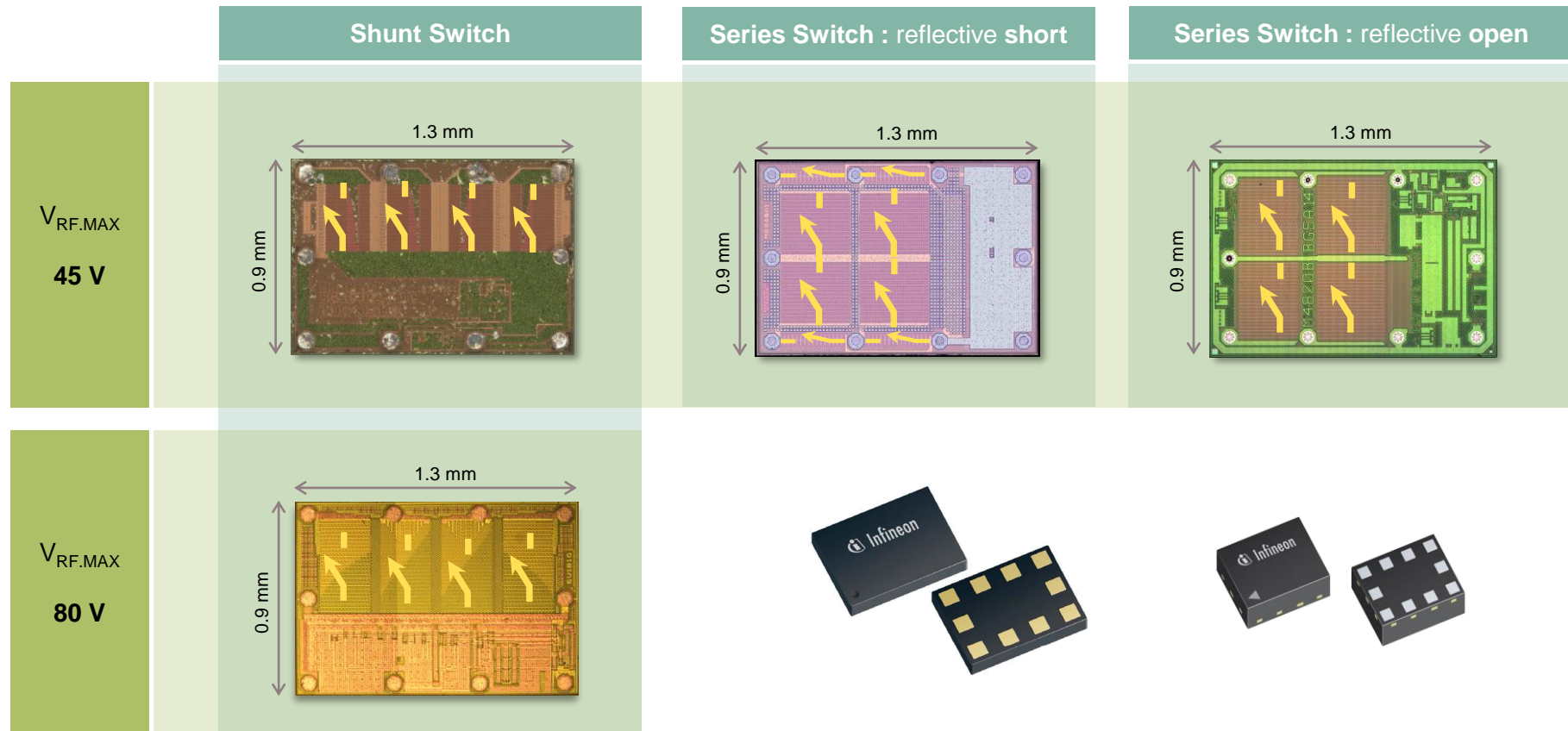
$$C_{bi} = \frac{i(i-1)}{2} \cdot C_{GND}$$



Tuner Products Examples



Antenna Tuner Examples





Part of your life. Part of tomorrow.